

Andrey P Odrinsky

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Photogalvanic Currents and Electrical Inhomogeneity of a 2D Structured Single Crystal of Ferroelectricâ€“Semiconductor. <i>Physics of the Solid State</i> , 2021, 63, 1288-1293.	0.2	0
2	Effect of Modification of the Contribution of the Thermal Emission of Localized Charges to the Relaxation of the Photoresponse of a TlGaSe ₂ Single Crystal. <i>Physics of the Solid State</i> , 2020, 62, 682-688.	0.2	4
3	Effect of deep native defects on ultrasound propagation in TlInS ₂ layered crystal. <i>Physica B: Condensed Matter</i> , 2016, 497, 86-92.	1.3	6
4	Photovoltaic currents and activity of structural defects in a ferroelectricâ€“semiconductor TlInS ₂ : La single crystal. <i>Physics of the Solid State</i> , 2016, 58, 716-722.	0.2	5
5	Identification of intrinsic deep level defects responsible for electret behavior in TlGaSe ₂ layered semiconductor. <i>Physica B: Condensed Matter</i> , 2016, 483, 82-89.	1.3	13
6	Photo-induced current transient spectroscopy of defects in single crystals of synthetic diamond. <i>Physics of the Solid State</i> , 2015, 57, 2279-2285.	0.2	0
7	Analysis of the photocurrent relaxation in semi-insulating GaAs in the temperature range of 150â€“200 K. <i>Semiconductors</i> , 2015, 49, 285-289.	0.2	3
8	Characterization of deep level defects and thermally stimulated depolarization phenomena in La-doped TlInS ₂ layered semiconductor. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	13
9	Photoelectric activity of defects in La-doped layered TlInS ₂ crystals. <i>Low Temperature Physics</i> , 2014, 40, 830-836.	0.2	7
10	Pyroelectric properties and structural defects of a layered TlInS ₂ crystal doped with lanthanum. <i>Physics of the Solid State</i> , 2014, 56, 2028-2034.	0.2	8
11	Photo-induced current transient spectroscopy of the ferroelectric-semiconductor TlGaSe ₂ . <i>Physics of the Solid State</i> , 2014, 56, 335-340.	0.2	7
12	Photoelectric activity of structural defects of a single crystal of the ferroelectric-semiconductor TlInS ₂ : La. <i>Physics of the Solid State</i> , 2014, 56, 1605-1609.	0.2	12
13	Carrier trapping and recombination in TlGaSe ₂ layered crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2013, 250, 160-168.	0.7	12
14	Photoinduced Current Transient Spectroscopy of TlInS ₂ Layered Crystals Doped with Er, B, and Tb Impurities. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 05FC08.	0.8	4
15	Transient spectroscopy of Rykkinâ€™s $\hat{\pm}$ centers. <i>Semiconductors</i> , 2011, 45, 857-860.	0.2	0
16	Photoinduced Current Transient Spectroscopy of TlInS ₂ Layered Crystals Doped with Er, B, and Tb Impurities. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 05FC08.	0.8	10
17	Photoinduced current transient spectroscopy of high-resistivity layered GaSe crystals. <i>Semiconductors</i> , 2010, 44, 854-856.	0.2	3
18	Investigation of defects in Cu(In,Ga)(S,Se) ₂ films using the photocurrent decay technique. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 371-374.	1.1	4

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19	Determination of the Concentration of Deep Levels in Semi-insulating CdS Single Crystals by Photoinduced-Current Transient Spectroscopy. <i>Semiconductors</i> , 2005, 39, 629.	0.2	6
20	A critical analysis of investigation of deep levels in high-resistivity CdS single crystals by photoelectric transient spectroscopy. <i>Semiconductors</i> , 2004, 38, 298-303.	0.2	7
21	Contactless Spectroscopy of Deep Levels in Semiconducting Materials: GaAs. <i>Spectroscopy Letters</i> , 1994, 27, 1281-1288.	0.5	3